Switch-mode Power Rectifier 60 V, 10 A

MBR10L60CTG, MBRF10L60CTG

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 10 A Total (5 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

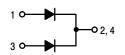
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

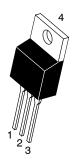


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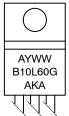
SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 60 VOLTS





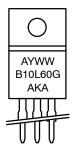
MARKING DIAGRAMS

TO-220 CASE 221A STYLE 6





TO-220 FULLPAK™ CASE 221D



A = Assembly Location

Y = Year
WW = Work Week
B10L60 = Device Code
G = Pb-Free Device
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current (Rated V_R) $T_C = 140^{\circ}C$	(Per Leg) (Per Device)	I _{F(AV)}	5 10	Α
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	200	Α
Operating Junction Temperature (Note 1)		T _J	-55 to +150	°C
Storage Temperature		T _{stg}	-65 to +175	°C
ESD Ratings: Machine Model = C Human Body Model = 3B			> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance			°C/W
MBR10L60CTG Junction-to-Case	$R_{ hetaJC}$	2.8	
Junction-to-Ambient	$R_{\theta JA}$	70	
MBRF10L60CTG Junction-to-Case		5.7	
Junction-to-Ambient	$R_{ hetaJC} \ R_{ hetaJA}$	75	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

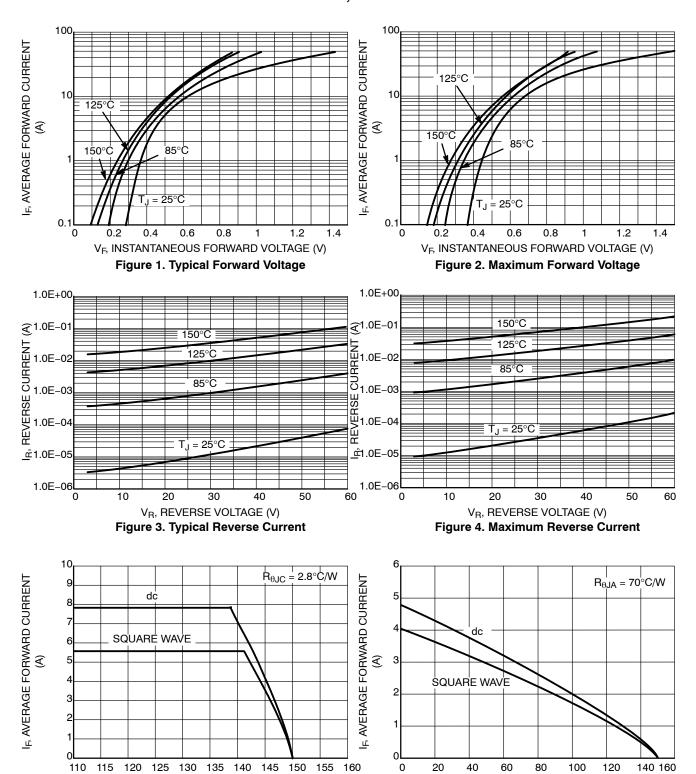
Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(I_F=5\text{ A},T_C=25^\circ\text{C})\\ &(I_F=5\text{ A},T_C=125^\circ\text{C})\\ &(I_F=10\text{ A},T_C=25^\circ\text{C})\\ &(I_F=10\text{ A},T_C=125^\circ\text{C}) \end{aligned} $	VF	0.49 0.43 0.60 0.53	0.57 0.49 0.66 0.61	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^{\circ}C$) (Rated DC Voltage, $T_C = 125^{\circ}C$)	i _R	77 33	220 60	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MBR10L60CTG	TO-220 (Pb-Free)	50 Units / Rail
MBRF10L60CTG	TO-220 FULLPAK (Pb-Free)	50 Units / Rail

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.



T_C, CASE TEMPERATURE (°C)

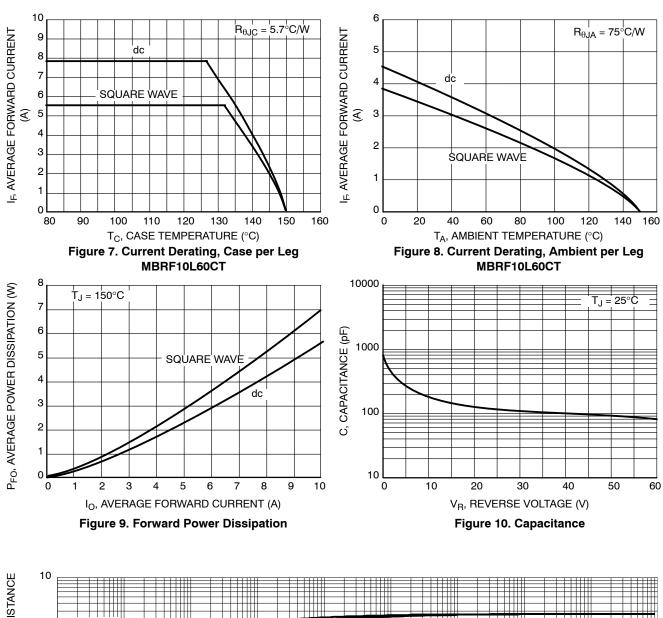
Figure 5. Current Derating, Case per Leg

MBR10L60CT

T_A, AMBIENT TEMPERATURE (°C)

Figure 6. Current Derating, Ambient per Leg

MBR10L60CT



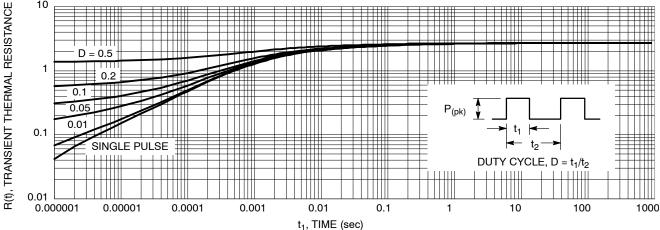


Figure 11. Thermal Response Junction-to-Case for MBR10L60CT

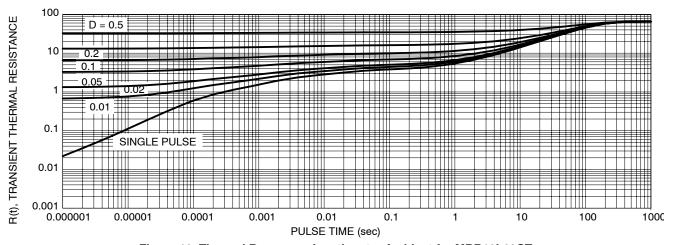


Figure 12. Thermal Response Junction-to-Ambient for MBR10L60CT

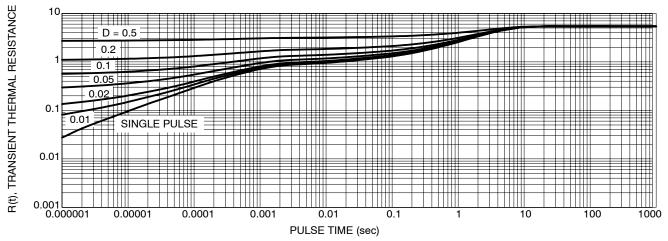


Figure 13. Thermal Response Junction-to-Case for MBRF10L60CT

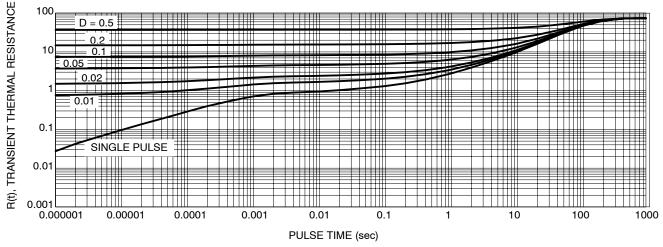


Figure 14. Thermal Response Junction-to-Ambient for MBRF10L60CT





SCALE 1:1

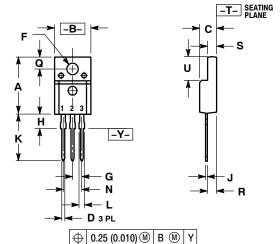
TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
С	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

MARKING DIAGRAMS



CATHODE
 ANODE

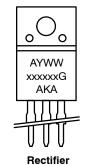
STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE

STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE 3. CATHODE

O xxxxxxG **AYWW**

Bipolar xxxxxx = Specific Device Code G = Pb-Free Package

Α = Assembly Location Υ = Year = Work Week WW



= Assembly Location

= Polarity Designator

Υ = Year = Work Week WW XXXXXX = Device Code = Pb-Free Package G

AKA

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DESCRIPTION:	TO-220 FULLPAK		PAGE 1 OF 1

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